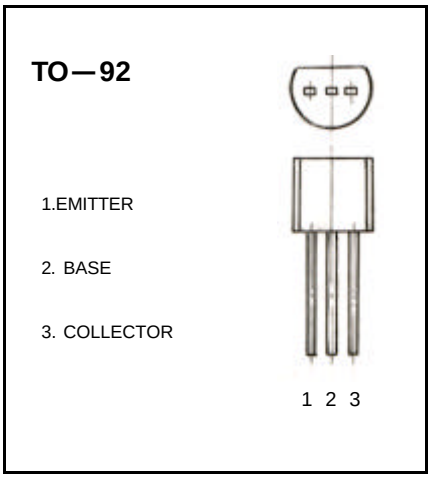
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

BC350 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM}: 0.3 W (Tamb=25℃)

Collector current

I_{CM}: -0.1 A

Collector-base voltage

$V_{(BR)CBO}$: -50 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= -100μA, I_E=0	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1mA, IB=0	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V, I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-35V, I_B=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -3V, I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-5 V, I_C= -2mA	40		450	
Collector-emitter saturation voltage	V_{CEsat}	I_C= -10mA, I_B= -1mA			-0.3	V
Base-emitter saturation voltage	V_{BEsat}	I_C= -10mA, I_B= -1mA			-1	V
Transition frequency	f_T	V_{CE}=-5 V,I_C=-10mA, f=30MHz	125			MHz

Typical Characteristics

BC350

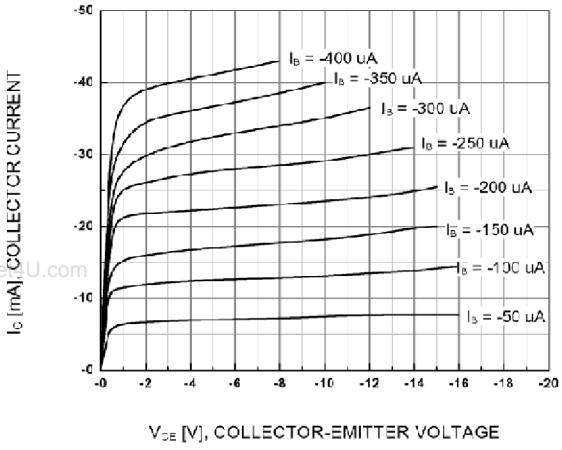


Figure 1. Static Characteristic

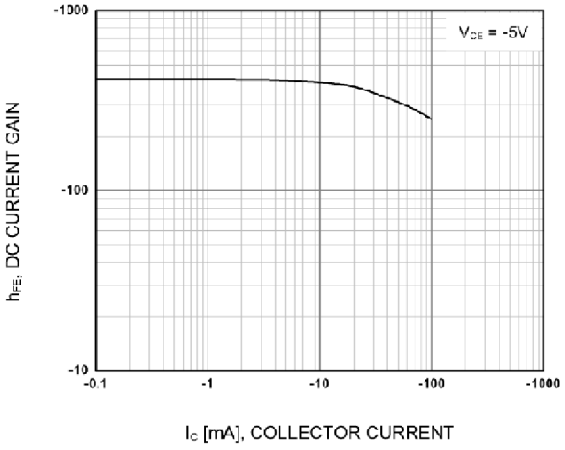


Figure 2. DC current Gain

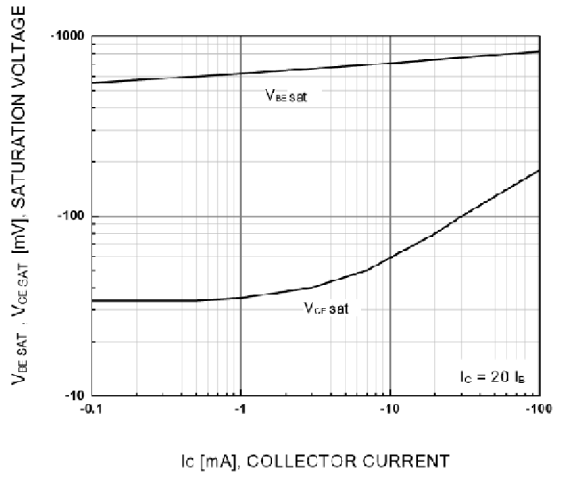


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

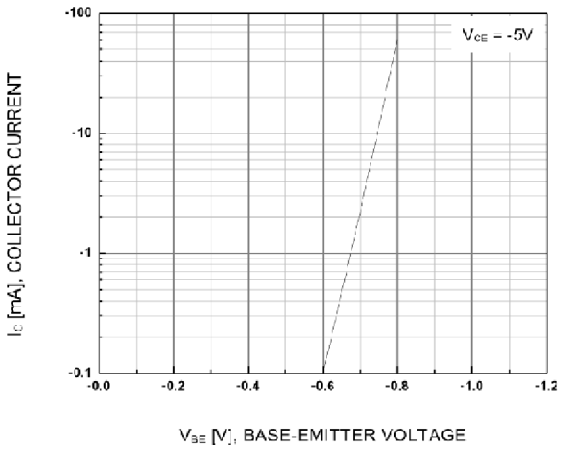


Figure 4. Base-Emitter On Voltage

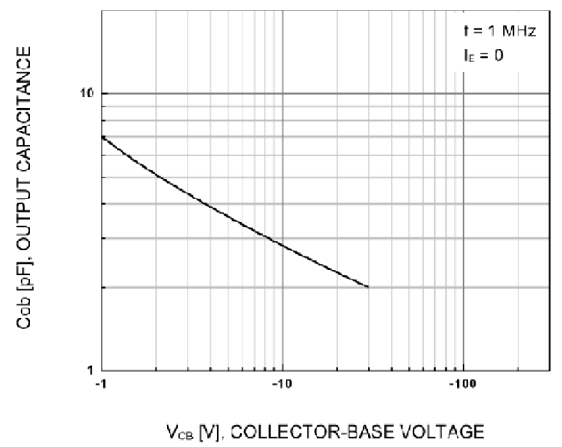


Figure 5. Collector Output Capacitance

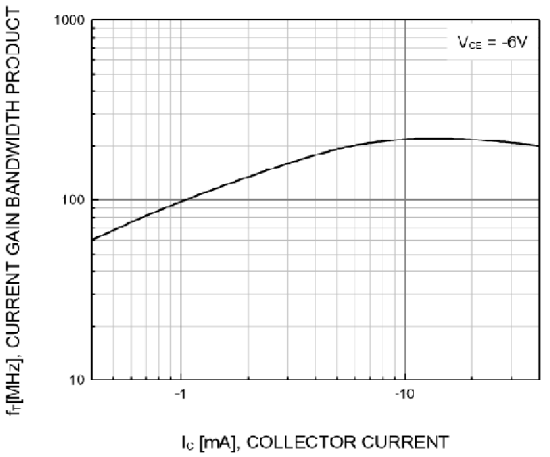
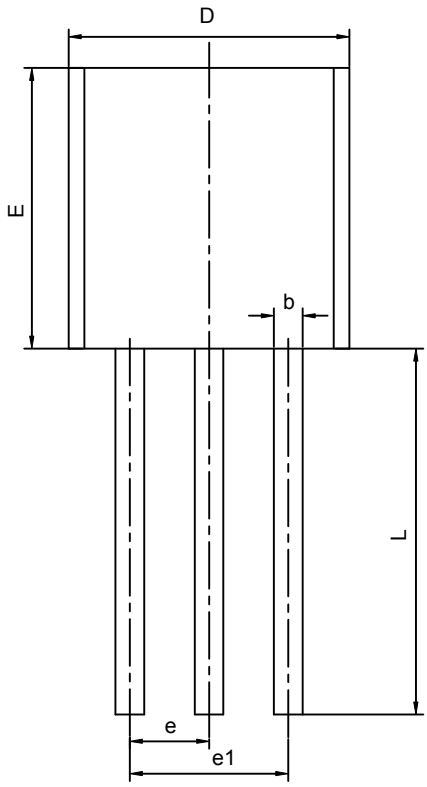
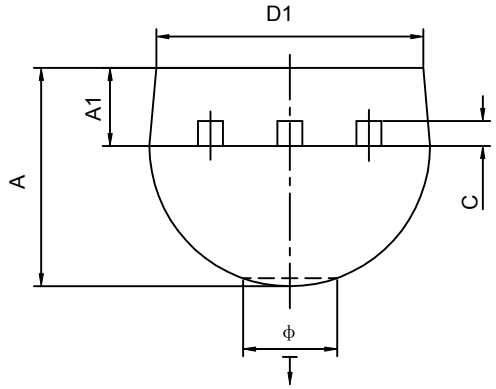


Figure 6. Current Gian Bandwidth Product

TO-92 PACKAGE OUTLINE DIMENSIONS





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ö		1.600		0.063
⊤	0.000	0.380	0.000	0.015